2SC5624

Silicon NPN Epitaxial
High Frequency Low Noise Amplifier

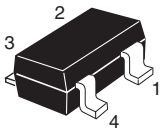
REJ03G0129-0200Z
(Previous ADE-208-978(Z))
Rev.2.00
Oct.21.2003

Features

- High gain bandwidth product
  f_T = 28 GHz typ.
- High power gain and low noise figure ;
  PG = 18 dB typ. , NF = 1.2 dB typ. at f = 1.8 GHz

Outline

CMPAK-4



1. Emitter
2. Collector
3. Emitter
4. Base

Note: Marking is “VH”-.

Absolute Maximum Ratings

(Ta = 25°C)

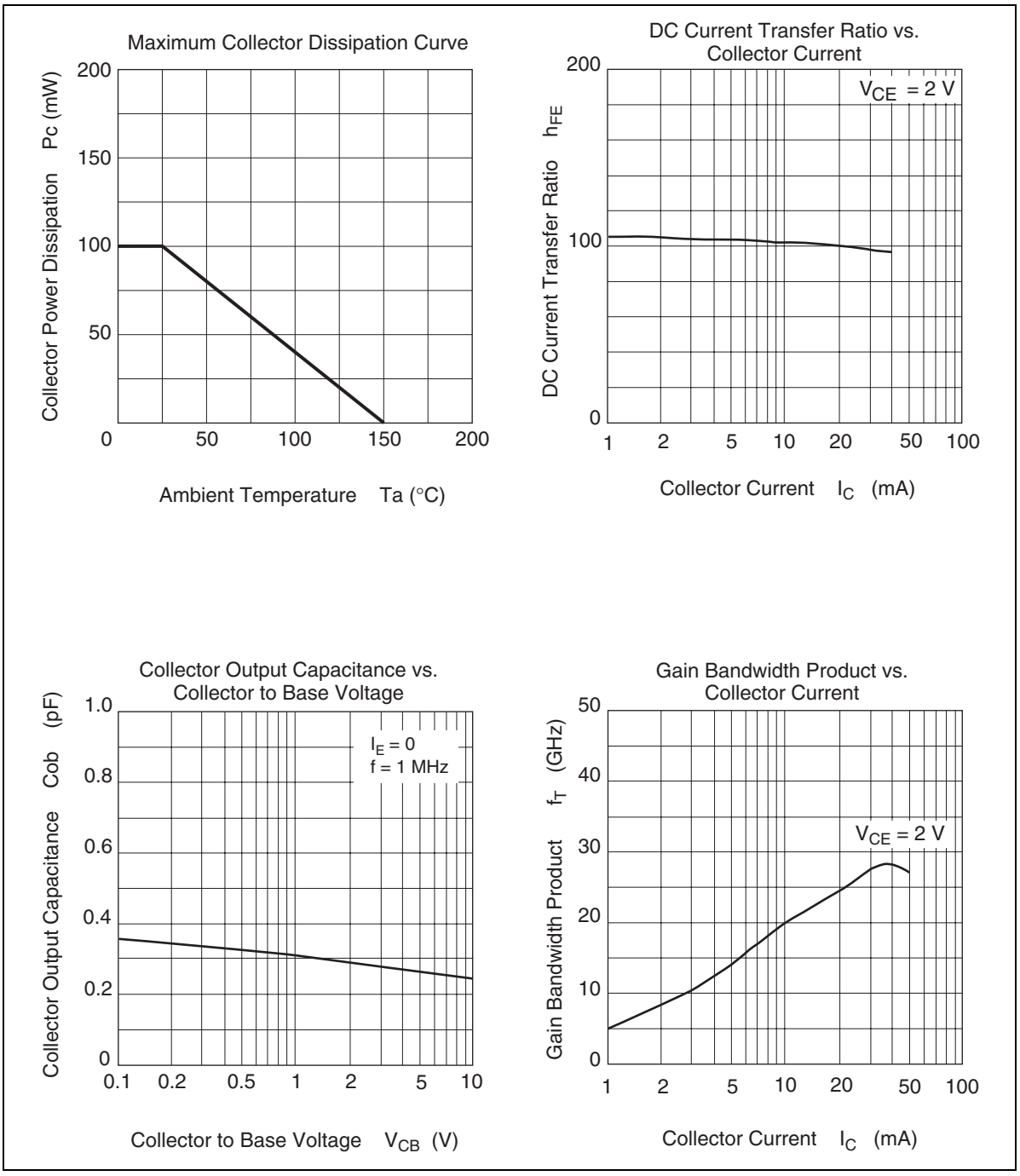
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	10	V
Collector to emitter voltage	V_{CEO}	3.5	V
Emitter to base voltage	V_{EBO}	0.8	V
Collector current	I_C	35	mA
Collector power dissipation	Pc	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics

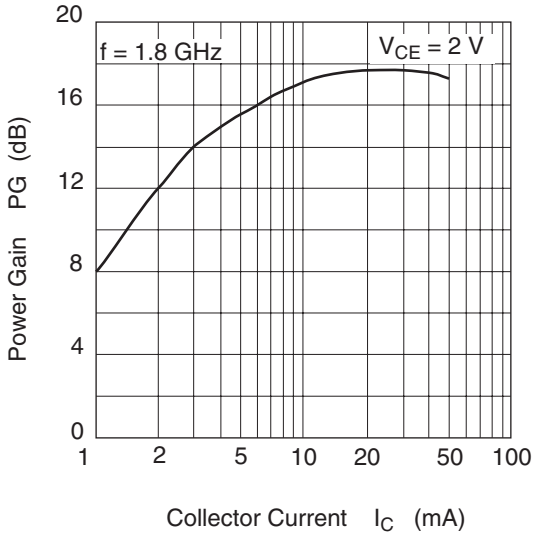
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	10	—	—	V	I_C = 10 µA , I_E = 0
Collector cutoff current	I_{CBO}	—	—	1	µA	V_{CB} = 8 V , I_E = 0
Collector cutoff current	I_{CEO}	—	—	1	µA	V_{CE} = 3 V , R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 0.8 V , I_C = 0
DC current transfer ratio	h_{FE}	80	120	160		V_{CE} = 2 V , I_C = 20 mA
Collector output capacitance	Cob	—	0.3	0.6	pF	V_{CB} = 2 V , I_E = 0 f = 1 MHz
Gain bandwidth product	f_T	25	28	—	GHz	V_{CE} = 2 V , I_C = 30 mA f = 2 GHz
Power gain	PG	14	18	—	dB	V_{CE} = 2 V, I_C = 30 mA f = 1.8 GHz
Noise figure	NF	—	1.2	1.6	dB	V_{CE} = 2 V, I_C = 5 mA f = 1.8 GHz

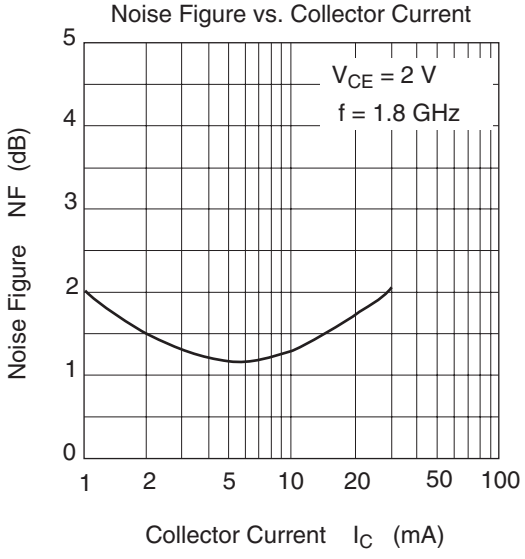
Main Characteristics



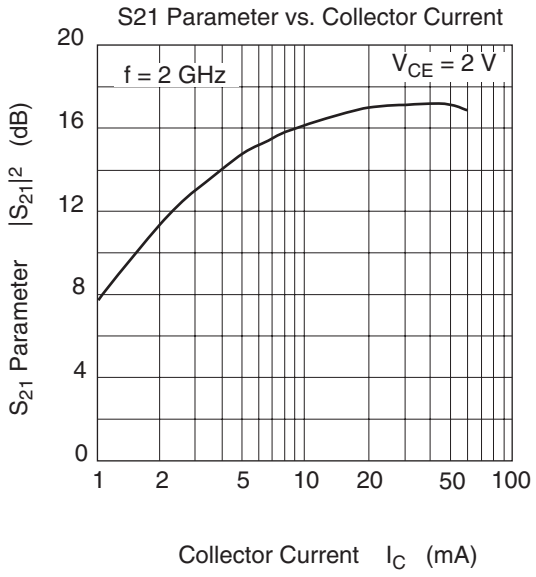
Power Gain vs. Collector Current



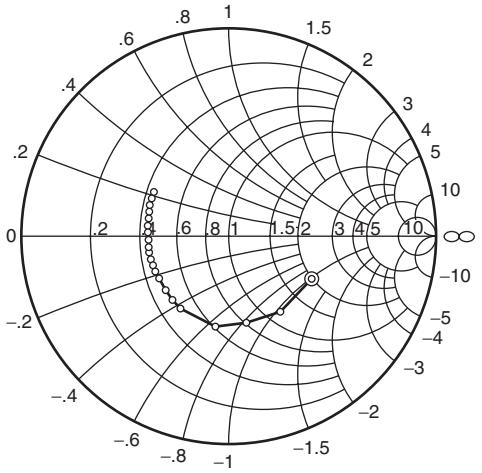
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current



S11 Parameter vs. Frequency

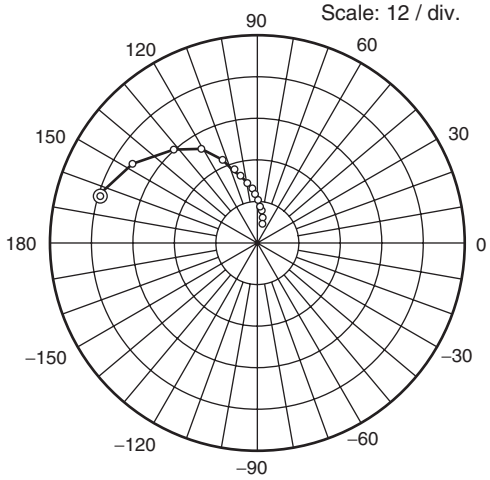


Condition ; V_{CE} = 2 V, I_C = 30 mA

100 to 3000 MHz (100 MHz step)

S21 Parameter vs. Frequency

Scale: 12 / div.

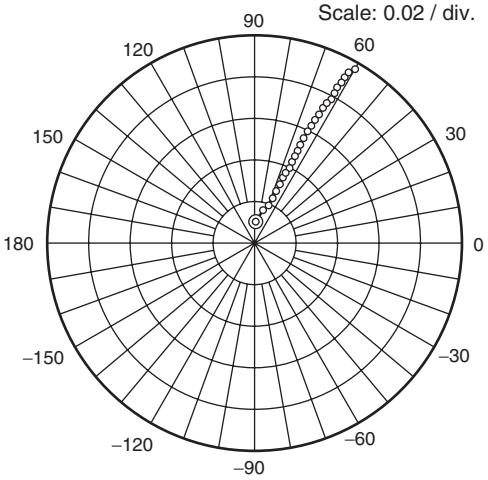


Condition ; V_{CE} = 2 V, I_C = 30 mA

100 to 3000 MHz (100 MHz step)

S12 Parameter vs. Frequency

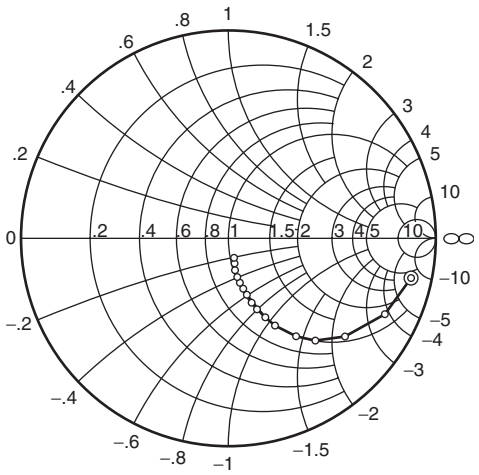
Scale: 0.02 / div.



Condition ; V_{CE} = 2 V, I_C = 30 mA

100 to 3000 MHz (100 MHz step)

S22 Parameter vs. Frequency



Condition ; V_{CE} = 2 V, I_C = 30 mA

100 to 3000 MHz (100 MHz step)

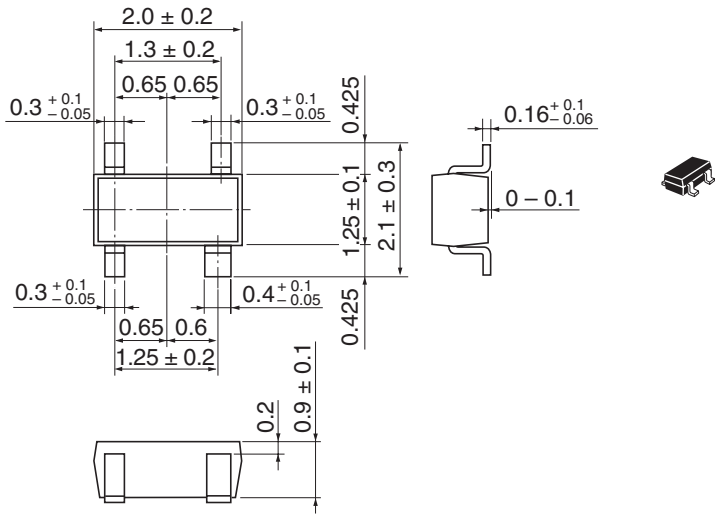
S parameter

(V_{CE} = 2 V, I_C = 30 mA, Zo = 50 Ω)

	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.445	–27.3	46.66	163.5	0.0055	83.8	0.904	–12.9
200	0.447	–54.4	42.27	147.1	0.0115	78.6	0.846	–26.8
300	0.439	–78.7	36.16	133.0	0.0165	73.6	0.750	–39.3
400	0.432	–98.8	30.59	122.2	0.0207	68.8	0.650	–48.8
500	0.424	–112.8	25.84	114.5	0.0246	67.1	0.561	–55.9
600	0.414	–124.3	22.15	108.9	0.0277	66.1	0.487	–61.4
700	0.407	–133.4	19.22	104.4	0.0307	65.0	0.426	–65.3
800	0.398	–141.5	16.94	100.8	0.0335	65.3	0.376	–68.6
900	0.390	–147.9	15.05	97.7	0.0372	64.4	0.335	–70.7
1000	0.386	–154.1	13.63	95.3	0.0398	65.1	0.301	–72.5
1100	0.381	–159.0	12.45	93.3	0.0420	65.2	0.273	–73.7
1200	0.377	–164.0	11.48	91.3	0.0452	65.0	0.250	–74.5
1300	0.371	–167.8	10.60	89.6	0.0480	64.5	0.229	–74.9
1400	0.370	–171.8	9.84	87.7	0.0509	64.7	0.213	–75.1
1500	0.367	–175.7	9.23	86.1	0.0535	64.3	0.197	–75.2
1600	0.368	–178.8	8.66	84.7	0.0567	64.1	0.186	–74.7
1700	0.370	178.0	8.16	83.4	0.0595	64.4	0.173	–74.7
1800	0.360	174.7	7.72	82.2	0.0623	64.3	0.164	–74.0
1900	0.365	172.0	7.33	80.8	0.0651	64.0	0.156	–73.6
2000	0.365	168.9	6.95	79.4	0.0682	63.8	0.148	–72.7
2100	0.362	166.8	6.66	78.2	0.0709	63.1	0.142	–72.0
2200	0.372	164.1	6.35	77.0	0.0737	63.0	0.135	–71.3
2300	0.370	160.9	6.08	75.6	0.0764	62.3	0.130	–70.8
2400	0.372	159.0	5.86	74.6	0.0795	62.3	0.125	–69.9
2500	0.378	156.6	5.64	73.5	0.0824	62.0	0.121	–68.7
2600	0.370	154.5	5.42	72.3	0.0848	61.6	0.117	–68.5
2700	0.382	152.2	5.24	71.3	0.0874	61.7	0.113	–67.1
2800	0.388	150.7	5.03	70.3	0.0906	60.7	0.109	–66.8
2900	0.387	147.6	4.86	69.0	0.0928	61.0	0.105	–65.7
3000	0.388	146.9	4.72	67.9	0.0964	59.7	0.102	–65.5

Package Dimensions

As of January, 2003
Unit: mm



Package Code	CMPAK-4(T)
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.006 g

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Colophon 1.0